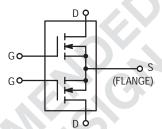
Product Is Not Recommended for New Design.

The next generation of higher performance products are in development. Visit our online Selector Guides (http://mot–sps.com/rf/sg/sg.html) for scheduled introduction dates.

# The RF MOSFET Line RF POWER Field-Effect Transistor

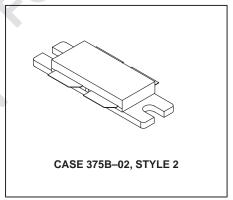
# N-Channel Enhancement-Mode Lateral MOSFET

- High Gain, Rugged Device
- Broadband Performance from HF to 1 GHz
- Bottom Side Source Eliminates DC Isolators, Reducing Common Mode Inductances



# **MRF185**

85 WATTS, 1.0 GHz 28 VOLTS LATERAL N-CHANNEL BROADBAND RF POWER MOSFET



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	65	Vdc
Gate-Source Voltage	VGS	±20	Vdc
Storage Temperature Range	T <sub>stg</sub>	- 65 to +150	°C
Operating Junction Temperature	TJ	200	°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	250 1.45	Watts W/°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	°C/W

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

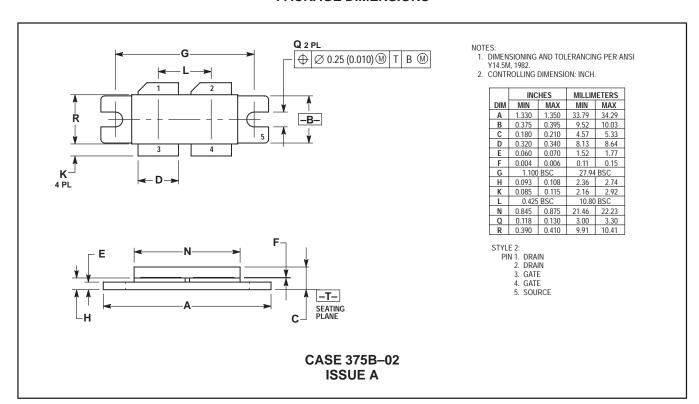
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage (V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 μAdc)	V(BR)DSS	65	_	_	Vdc
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 28 V, V <sub>GS</sub> = 0 V)	IDSS	_	_	1	μAdc
Gate-Source Leakage Current (VGS = 20 V, VDS = 0 V)	lgss	-	_	1	μAdc

 $NOTE - \underline{\textbf{CAUTION}}$  - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

## **ELECTRICAL CHARACTERISTICS – continued** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					
Gate Quiescent Voltage (V <sub>DS</sub> = 26 V, I <sub>D</sub> = 300 mA per side)	VGS(Q)	3	4	5	Vdc
Delta Quiescent Voltage between sides (V <sub>DS</sub> = 26 V, I <sub>D</sub> = 300 mA per side)	∆V <sub>GS(Q)</sub>	-	0.15	0.3	Vdc
Drain–Source On–Voltage (VGS = 10 V, I <sub>D</sub> = 3 A per side)	V <sub>DS(on)</sub>	-	0.75	1	Vdc
Forward Transconductance (V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 A per side)	9fs	1.6	2	-	S
DYNAMIC CHARACTERISTICS					
Output Capacitance (V <sub>DS</sub> = 28 V, V <sub>GS</sub> = 0 V, f = 1 MHz)	C <sub>oss</sub>		38	_	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 28 V, V <sub>GS</sub> = 0 V, f = 1 MHz)	C <sub>rss</sub>	-	4.6	6	pF
FUNCTIONAL CHARACTERISTICS				•	•
Common Source Power Gain (V <sub>DD</sub> = 28 V, P <sub>out</sub> = 85 W, f = 960 MHz, I <sub>DQ</sub> = 600 mA)	G <sub>ps</sub>	11	14	-	dB
Drain Efficiency (V <sub>DD</sub> = 28 V, P <sub>out</sub> = 85 W, f = 960 MHz, I <sub>DQ</sub> = 600 mA)	η	45	53	-	%
Load Mismatch (V <sub>DD</sub> = 28 Vdc, P <sub>out</sub> = 85 W, f = 960 MHz, I <sub>DQ</sub> = 600 mA, Load VSWR 5:1 at All Phase Angles)	Ψ	No Degradation in Output Power			

## **PACKAGE DIMENSIONS**



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